STARPOWER

SEMICONDUCTOR **IGBT**

GD75FSY120L3S

1200V/75A 6 in one-package

General Description

STARPOWER IGBT Power Module provides ultra low conduction loss as well as short circuit ruggedness. They are designed for the applications such as general inverters and UPS.

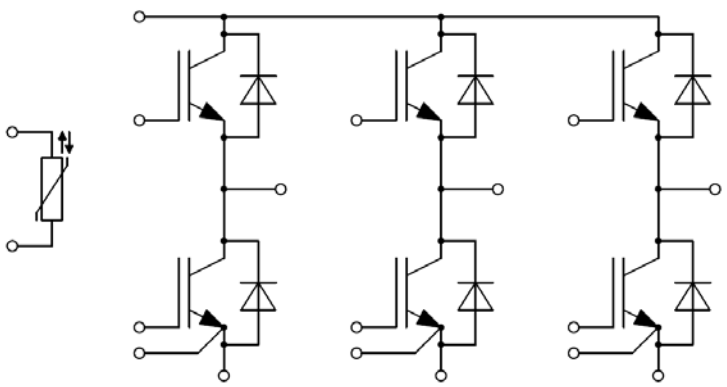
Features

- Low $V_{CE(sat)}$ Trench IGBT technology
- 10μs short circuit capability
- $V_{CE(sat)}$ with positive temperature coefficient
- Maximum junction temperature 175°C
- Low inductance case
- Fast & soft reverse recovery anti-parallel FWD
- Isolated heatsink using DBC technology

Typical Applications

- Inverter for motor drive
- AC and DC servo drive amplifier
- Uninterruptible power supply

Equivalent Circuit Schematic



Absolute Maximum Ratings T_C=25°C unless otherwise noted

IGBT

Symbol	Description	Value	Unit
V_{CES}	Collector-Emitter Voltage	1200	V
V_{GES}	Gate-Emitter Voltage	±20	V
I_C	Collector Current @ T_C=25°C @ T_C=100°C	150 75	A
I_{CM}	Pulsed Collector Current t_p=1ms	150	A
P_D	Maximum Power Dissipation @ T_j=175°C	576	W

Diode

Symbol	Description	Values	Unit
V_{RRM}	Repetitive Peak Reverse Voltage	1200	V
I_F	Diode Continuous Forward Current	75	A
I_{FM}	Diode Maximum Forward Current t_p=1ms	150	A

Module

Symbol	Description	Value	Unit
T_{jmax}	Maximum Junction Temperature	175	°C
T_{jop}	Operating Junction Temperature	-40 to +150	°C
T_{STG}	Storage Temperature Range	-40 to +125	°C
V_{ISO}	Isolation Voltage RMS,f=50Hz,t=1min	2500	V

IGBT Characteristics T_C=25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	I_C=75A,V_{GE}=15V, T_j=25°C		1.65	2.10	V
		I_C=75A,V_{GE}=15V, T_j=125°C		1.95		
		I_C=75A,V_{GE}=15V, T_j=150°C		2.00		
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	I_C=1.88mA,V_{CE}=V_{GE}, T_j=25°C	5.2	6.0	6.8	V
I_{CES}	Collector Cut-Off Current	V_{CE}=V_{CES},V_{GE}=0V, T_j=25°C			1.0	mA
I_{GES}	Gate-Emitter Leakage Current	V_{GE}=V_{GES},V_{CE}=0V, T_j=25°C			100	nA
R_{Gint}	Internal Gate Resistance			2.0		Ω
C_{ies}	Input Capacitance	V_{CE}=30V,f=1MHz, V_{GE}=0V		7.15		nF
C_{res}	Reverse Transfer Capacitance			0.23		nF
Q_G	Gate Charge	V_{GE}=-15…+15V		0.48		μC
$t_{d(on)}$	Turn-On Delay Time	V_{CC}=600V,I_C=75A, R_G=5.1Ω,V_{GE}=±15V, T_j=25°C		219		ns
t_r	Rise Time			42		ns
$t_{d(off)}$	Turn-Off Delay Time			271		ns
t_f	Fall Time			261		ns
E_{on}	Turn-On Switching Loss			2.95		mJ
E_{off}	Turn-Off Switching Loss			4.70		mJ
$t_{d(on)}$	Turn-On Delay Time	V_{CC}=600V,I_C=75A, R_G=5.1Ω,V_{GE}=±15V, T_j=125°C		220		ns
t_r	Rise Time			46		ns
$t_{d(off)}$	Turn-Off Delay Time			289		ns
t_f	Fall Time			397		ns
E_{on}	Turn-On Switching Loss			4.00		mJ
E_{off}	Turn-Off Switching Loss			7.65		mJ
$t_{d(on)}$	Turn-On Delay Time	V_{CC}=600V,I_C=75A, R_G=5.1Ω,V_{GE}=±15V, T_j=150°C		222		ns
t_r	Rise Time			46		ns
$t_{d(off)}$	Turn-Off Delay Time			295		ns
t_f	Fall Time			410		ns
E_{on}	Turn-On Switching Loss			4.40		mJ
E_{off}	Turn-Off Switching Loss			8.41		mJ
I_{SC}	SC Data	t_P≤10μs,V_{GE}=15V, T_j=150°C,V_{CC}=900V, V_{CEM}≤1200V		300		A

Diode Characteristics T_C=25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V_F	Diode Forward Voltage	I_F=75A,V_{GE}=0V,T_j=25°C		1.70	2.15	V
		I_F=75A,V_{GE}=0V,T_j=125°C		1.65		
		I_F=75A,V_{GE}=0V,T_j=150°C		1.65		
Q_r	Recovered Charge	V_R=600V,I_F=75A, -di/dt=1400A/μs,V_{GE}=-15V T_j=25°C		5.0		μC
I_{RM}	Peak Reverse Recovery Current			81		A
E_{rec}	Reverse Recovery Energy			3.40		mJ
Q_r	Recovered Charge	V_R=600V,I_F=75A, -di/dt=1400A/μs,V_{GE}=-15V T_j=125°C		11.0		μC
I_{RM}	Peak Reverse Recovery Current			97		A
E_{rec}	Reverse Recovery Energy			6.02		mJ
Q_r	Recovered Charge	V_R=600V,I_F=75A, -di/dt=1400A/μs,V_{GE}=-15V T_j=150°C		12.5		μC
I_{RM}	Peak Reverse Recovery Current			106		A
E_{rec}	Reverse Recovery Energy			6.62		mJ

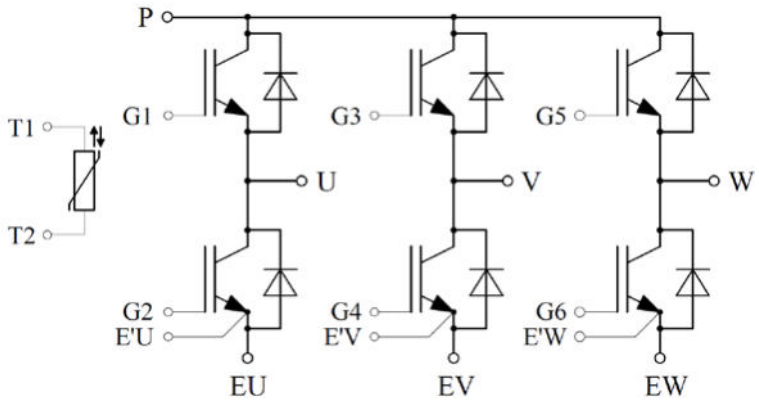
NTC Characteristics T_C=25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
R_{25}	Rated Resistance			5.0		kΩ
ΔR/R	Deviation of R_{100}	T_C=100°C,R_{100}=493.3Ω	-5		5	%
P_{25}	Power Dissipation				20.0	mW
$B_{25/50}$	B-value	$R_2=R_{25}\exp[B_{25/50}(1/T_2-1/(298.15K))]$		3375		K

Module Characteristics T_C=25°C unless otherwise noted

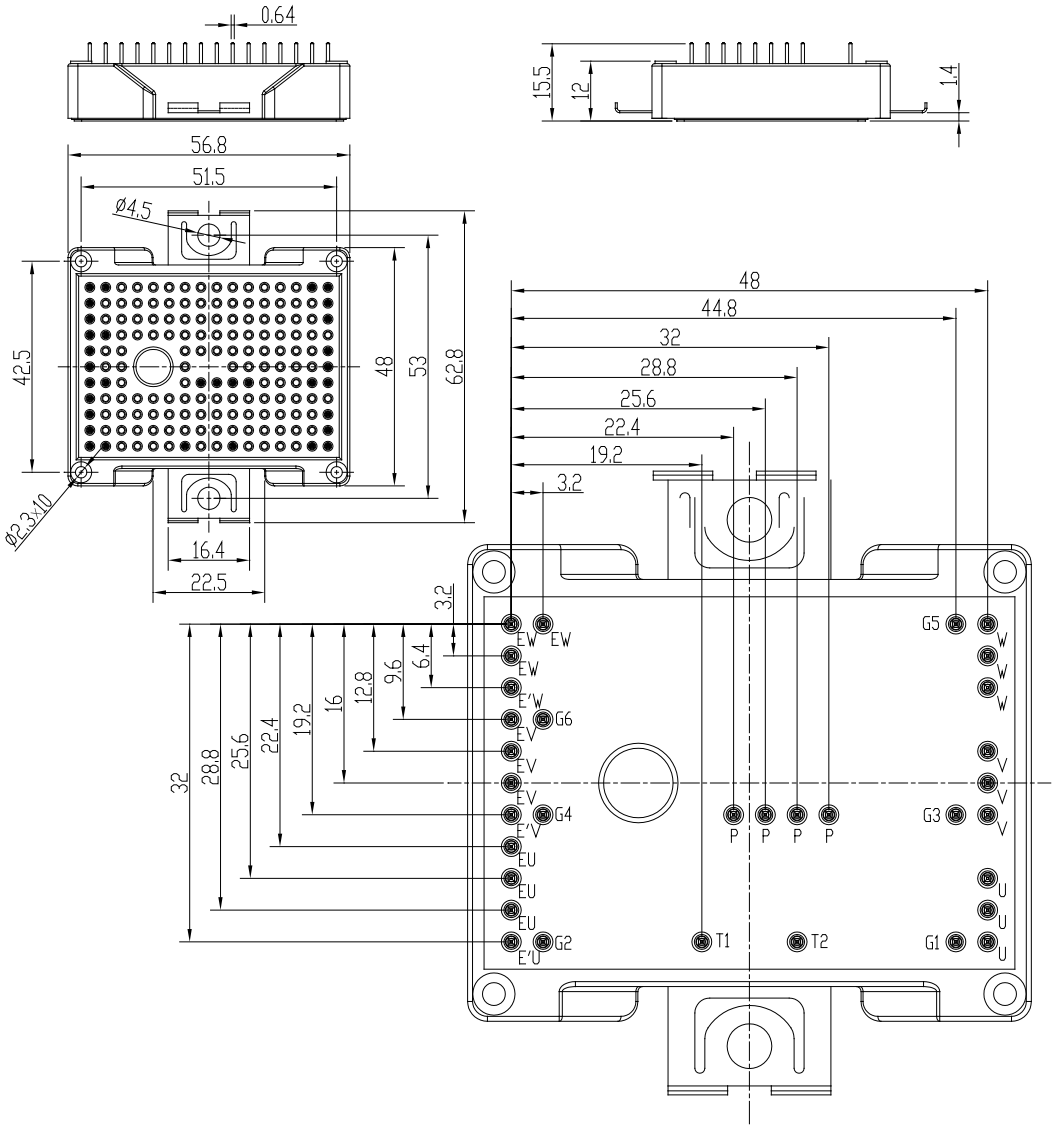
Symbol	Parameter	Min.	Typ.	Max.	Unit
L_{CE}	Stray Inductance		40		nH
$R_{CC'+EE'}$	Module Lead Resistance, Terminal to Chip		4.00		mΩ
R_{thJC}	Junction-to-Case (per IGBT) Junction-to-Case (per Diode)		0.236 0.405	0.260 0.446	K/W
R_{thCH}	Case-to-Heatsink (per IGBT) Case-to-Heatsink (per Diode) Case-to-Heatsink (per Module)		0.351 0.603 0.037		K/W
F	Mounting Force Per Clamp	40		80	N
G	Weight of Module		39		g

Circuit Schematic



Package Dimensions

Dimensions in Millimeters



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